
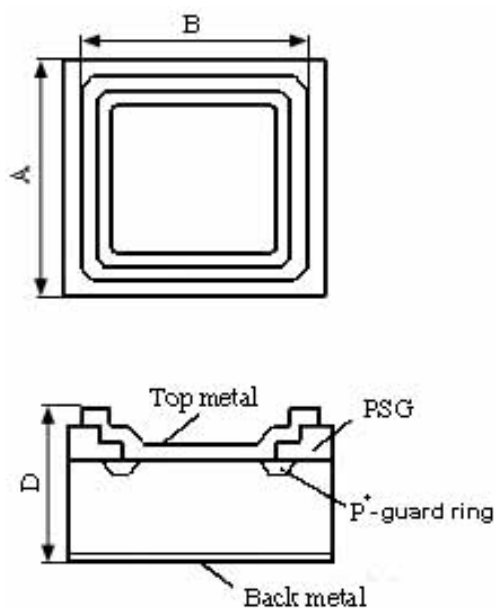


SCHOTTKY DIODES KDS- 2131A1.



Rev.1. March. 2010

 VSP-MIKRON	30A/15V. Die Size-106*158mil.			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	V_B	V	18	20
Average Rectified Forward Current	$I_{F(AV)}$	A	30,0	-
DC Forward Voltage @ $25^\circ C, I_F=30,0A$	V_F	V	0,38	0,365
Maximum Reverse Current @ $25^\circ C, V_R=15V$ @ $25^\circ C, V_R=20V$ @ $100^\circ C, V_R=15V$	I_R	MA	15,0 - 500,0	10,0 20,0 450,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	300	-
Peak Repetitive Reverse Surge Current @ $2,0\mu s, f=1kHz., T_J < 125^\circ C.$	I_{RRM}	A	5,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	± 8 (contact)	
Voltage Rate of Change	dV/dt	V/ μS	10.000	
Operating Junction Temperature	T_J	$^\circ C$	125	



DIM	ITEM	μm
A_x A_y	Wafer Form Die Size	4000 2700
B_x B_y	Top Metal Size	3820 2520
D	Thickness	350max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;
 b) **Al-Ni-Ag** – for Soldering.
Backside metal: **Ti-Ni-Ag**.